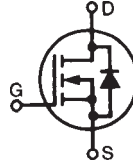


# Polar VHV™ Power MOSFET

**IXTA2R4N120P**  
**IXTH2R4N120P**  
**IXTP2R4N120P**

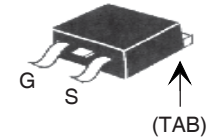
**V<sub>DSS</sub> = 1200V**  
**I<sub>D25</sub> = 2.4A**  
**R<sub>DS(on)</sub> ≤ 7.5Ω**

N-Channel Enhancement Mode  
Avalanche Rated

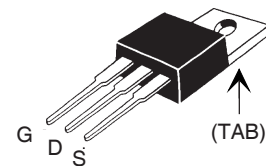


Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	1200	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C, R <sub>GS</sub> = 1MΩ	1200	V
V <sub>GSS</sub>	Continuous	±20	V
V <sub>GSM</sub>	Transient	±30	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	2.4	A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, pulse width limited by T <sub>JM</sub>	6	A
I <sub>A</sub>	T <sub>C</sub> = 25°C	2.4	A
E <sub>AR</sub>	T <sub>C</sub> = 25°C	20	mJ
E <sub>AS</sub>	T <sub>C</sub> = 25°C	200	mJ
dV/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150°C	10	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25°C	125	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	1.6mm (0.062) from case for 10s	300	°C
T <sub>SOLD</sub>	Plastic body for 10s	260	°C
M <sub>d</sub>	Mounting torque (TO-220, TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-263	2.5	g
	TO-220	3.0	g
	TO-247	6.0	g

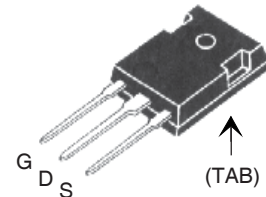
TO-263 (IXTA)



TO-220 (IXTP)



TO-247 (IXTH)



G = Gate      D = Drain  
S = Source    TAB = Drain

## Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

## Advantages

- Easy to mount
- Space savings
- High power density

## Applications:

- Switched-mode and resonant-mode power supplies
- DC-DC Converters
- Laser Drivers
- AC and DC motor controls
- Robotics and servo controls

Symbol	Test Conditions (T <sub>J</sub> = 25°C, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	1200		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2.5		4.5 V
I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±50 nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> V <sub>GS</sub> = 0V T <sub>J</sub> = 125°C			5 μA 300 μA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Note 1	6.5	7.5	Ω

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max
$g_{fs}$	$V_{DS} = 20\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1	1.2	2.0	S
$C_{iss}$ $C_{oss}$ $C_{rss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		1207	pF
			57	pF
			11.2	pF
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 18\Omega$ (External)		22	ns
			25	ns
			70	ns
			32	ns
$Q_{g(on)}$ $Q_{gs}$ $Q_{gd}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		37	nC
			6	nC
			20	nC
$R_{thJC}$ $R_{thCS}$	(TO-220) (TO-247)		0.50 0.21	$1.0^\circ\text{C/W}$ $^\circ\text{C/W}$ $^\circ\text{C/W}$

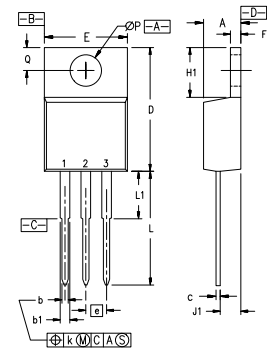
**Source-Drain Diode**

**Characteristic Values**  
( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

Symbol	Test Conditions	Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			2.4 A
$I_{SM}$	Repetitive			7.2 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 2.4\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ , $V_R = 100\text{V}$ , $V_{GS} = 0\text{V}$		920	ns

Note 1: Pulse test,  $t \leq 300 \mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

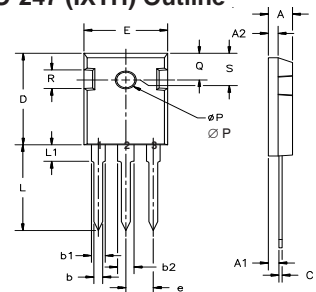
**TO-220 (IXTP) Outline**



Pins: 1 - Gate 2 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
$\varnothing P$	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

**TO-247 (IXTH) Outline**



Terminals: 1 - Gate 2 - Drain  
3 - Source

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
$\varnothing P$	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

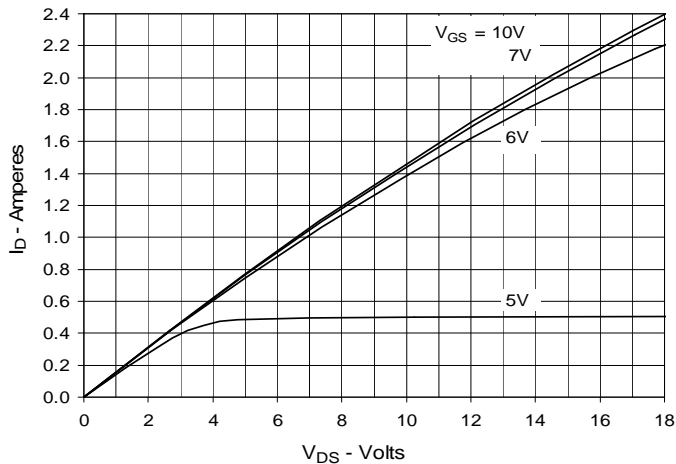
**TO-263 (IXTA) Outline**

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A <sub>1</sub>	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b <sub>2</sub>	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c <sub>2</sub>	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D <sub>1</sub>	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E <sub>1</sub>	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L <sub>1</sub>	.090	.110	2.29	2.79
L <sub>2</sub>	.040	.055	1.02	1.40
L <sub>3</sub>	.050	.070	1.27	1.78
L <sub>4</sub>	0	.005	0	0.13

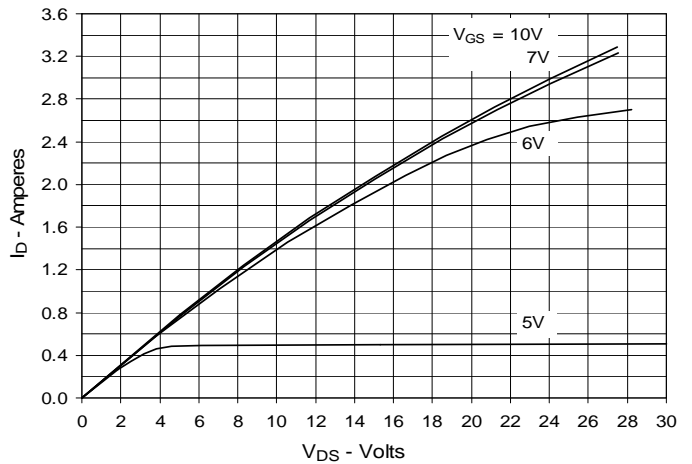
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585	7,005,734B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692	7,063,975B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728B1	6,583,505	6,710,463	6,771,478B2	7,071,537	

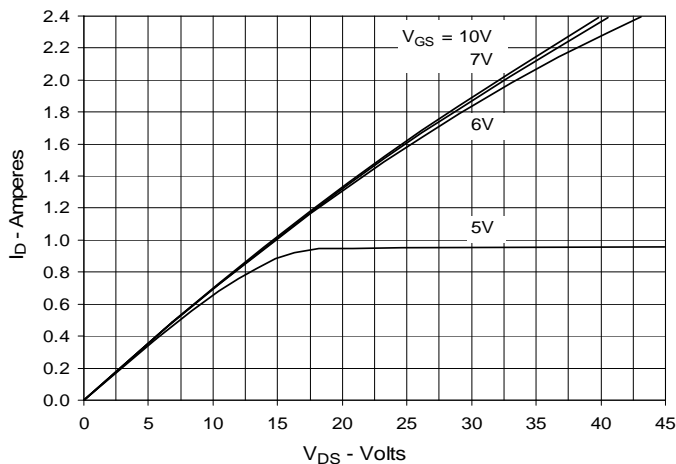
**Fig. 1. Output Characteristics @ 25°C**



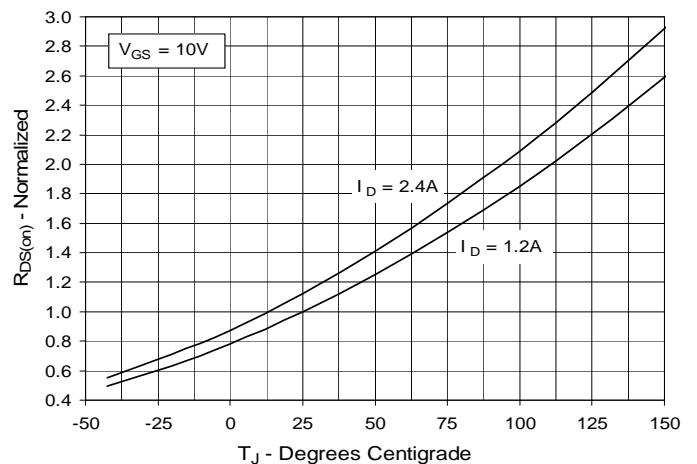
**Fig. 2. Extended Output Characteristics @ 25°C**



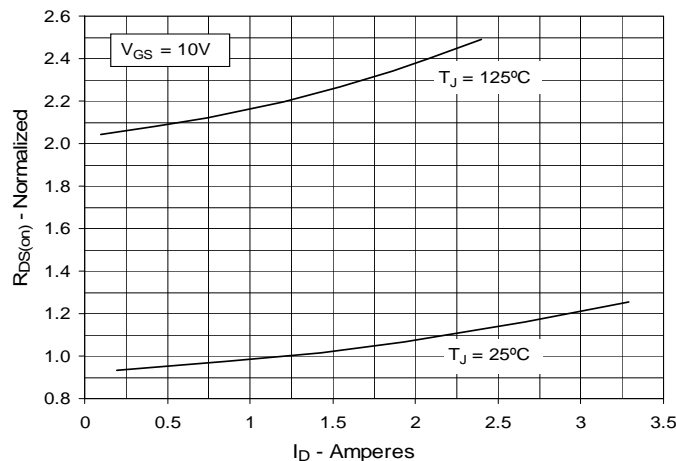
**Fig. 3. Output Characteristics @ 125°C**



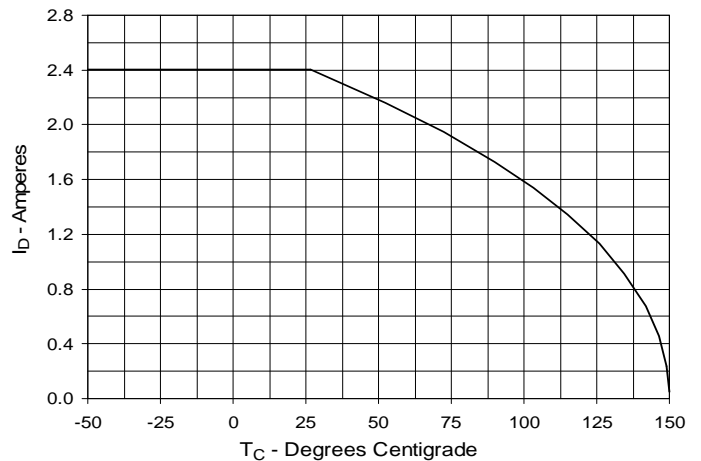
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 1.2A$  Value vs. Junction Temperature**



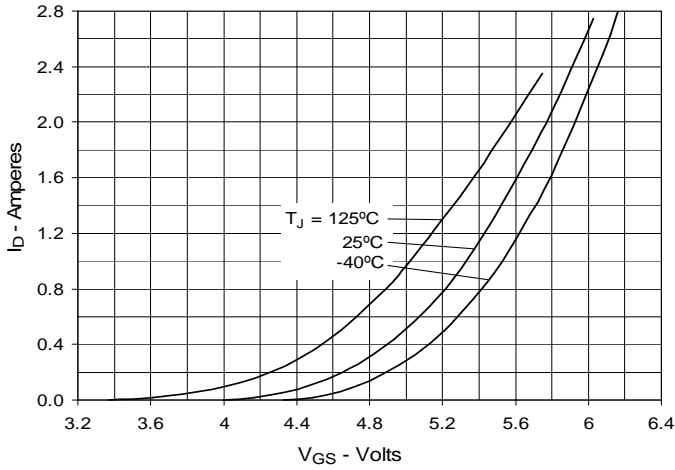
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 1.2A$  Value vs. Drain Current**



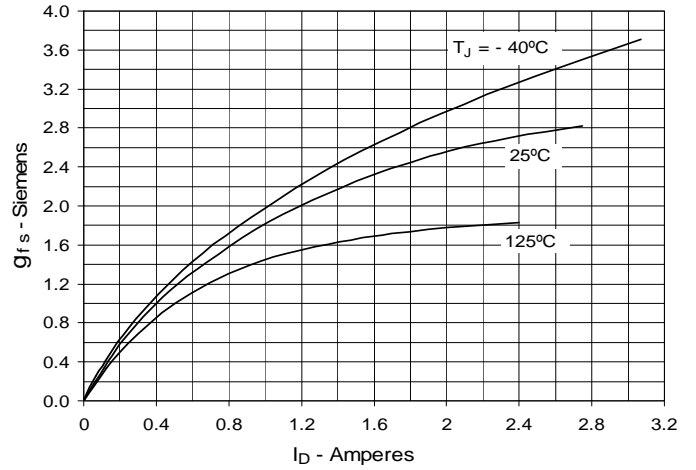
**Fig. 6. Maximum Drain Current vs. Case Temperature**



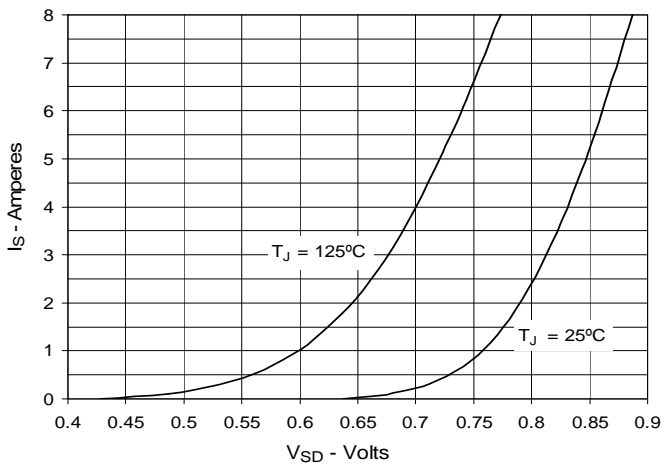
**Fig. 7. Input Admittance**



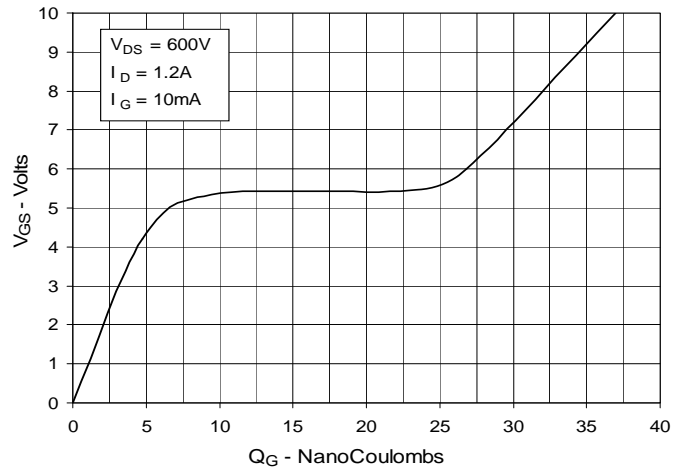
**Fig. 8. Transconductance**



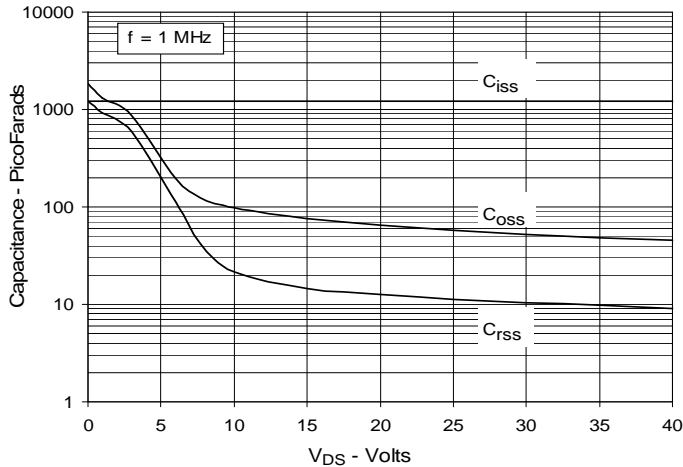
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Impedance**

